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**CONFIRMATION NO. 5622** 

met Allowance Verified and Acknowledged Examiner's Signature Mitials  ADDRESS 26263  TITLE	Bib Data Sneet									
Junichi Sato, Tokyo, JAPAN; Setsuo Usui, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yashifumi Mori, Chiba, JAPAN; Hideharu Nakajima, Kanagawa, JAPAN; Hideharu Nakajima, Kanagawa, JAPAN;  "CONTINUING DATA This application is a DIV of 09/946,898 09/05/2001 PAT 6,746,942  "FOREIGN APPLICATIONS JAPAN P2000-269298 09/05/2000 JAPAN P2000-269274 09/05/2000 JAPAN P2000-269210 199/05/2000 JAPAN P200			<b>DATE</b> 04/21/2004	_ · · · -				DOCKET NO.		
Setsuo Usui, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Hideharu Nakajima, Kanagawa, JAPAN;  "CONTINUING DATA  This application is a DIV of 09/946,898 09/05/2001 PAT 6,746,942  "FOREIGN APPLICATIONS "***  JAPAN P2000-26928 09/05/2000 JAPAN P2000-269274 09/05/2000 JAPAN P2001-244163 08/10/2001  IF REQUIRED, FOREIGN FILING LICENSE GRANTED  "09/02/2004  Foreign Priority claimed  "09/02/2004  Foreign Priority claimed  "Yes on Met after Country Milowance  "Nerified and Acknowledged Examiner's Signature Acknowledged Examiner	APPLICANTS									
This application is a DIV of 09/946,898 09/05/2001 PAT 6,746,942  **FOREIGN APPLICATIONS************************************	Setsuo Usui, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yoshifumi Mori, Chiba, JAPAN;									
JAPAN P2000-269298 09/05/2000 JAPAN P2000-269274 09/05/2000 JAPAN P2001-244163 08/10/2001  Foreign Priority claimed	** CONTINUING DATA **********************************									
JAPAN P2000-269298 09/05/2000 JAPAN P2000-269274 09/05/2000 JAPAN P2001-244163 08/10/2001  Foreign Priority claimed Jyes no STATE OR COUNTRY DRAWING CLAIMS 2  STATE OR COUNTRY DRAWING CLAIMS 2  TOTAL CLAIMS 2  LAIMS 2  TITLE  Semiconductor thin film and method of fabricating semiconductor thin film, apparatus for fabricating single crystal semiconductor thin film substrate, and semiconductor device  FILING FEE RECEIVED 770  FEES: Authority has been given in Paper No to charge/credit DEPOSIT ACCOUNT No for following:    All Fees   1.16 Fees (Filing )     1.17 Fees (Processing Ext. of lime)     1.18 Fees (Issue )     Other										
JAPAN P2000-269274 09/05/2000 JAPAN P2000-269261 09/05/2000 JAPAN P2001-244163 08/10/2001  IF REQUIRED, FOREIGN FILING LICENSE GRANTED  ** 09/02/2004  Foreign Priority claimed 35 USC 119 (a-d) conditions	** FOREIGN APPLICATIONS ************************************									
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35 USC 119 (a-d) conditions  yes  no  Met after  COUNTRY  DRAWING										
TITLE Semiconductor thin film and method of fabricating semiconductor thin film, apparatus for fabricating single crystal semiconductor thin film, and method of fabricating single crystal thin film, single crystal thin film substrate, and semiconductor device  FILING FEE RECEIVED 770  FEES: Authority has been given in Paper No to charge/credit DEPOSIT ACCOUNT No for following:    All Fees     1.17 Fees ( Processing Ext. of time )   1.18 Fees ( Issue )   Other	35 USC 119 (a-d) conditions				DRA	DRAWING CLAIMS		CLAIMS		
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